L Number	Hits	Search Text	DB	Time stamp
4	165	((thin adj film adj transistor) tft) same (cmos	USPAT;	2004/06/09 10:24
		complementary) same (channel with (impurit\$4 dop\$4) with	US-PGPUB	
		("p-type" "p type" "p-doped" "p doped" boron))		
5	24	((channel with (impurit\$4 dop\$4) with ("p-type" "p type"	EPO; JPO;	2004/06/09 12:27
		"p-doped" "p doped" boron))) and ((thin adj film adj	DERWENT;	
		transistor) tft) and (cmos complementary)	IBM_TDB	
6	122	(((channel near4 (impurit\$4 dop\$4)) with ("p-type" "p type"	EPO; JPO;	2004/06/09 12:42
		"p-doped" "p doped" boron))) same ((thin adj film adj	DERWENT;	
		transistor) tft cmos complementary)	IBM_TDB	
7	82	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls.	USPAT;	2004/06/09 13:11
		345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and	US-PGPUB	
		((thin adj film adj transistor) tft) and ((cmos		İ
		complementary) same (channel with (impurit\$4 dop\$4) with		
		("p-type" "p type" "p-doped" "p doped" boron)))		
-	12	6635521.pn. 5403764.pn. 5563427.pn. 5643826.pn.	USPAT;	2004/06/08 10:49
		5751037.pn. 5824573.pn. 5885861.pn. 6001677.pn.	US-PGPUB	
		6033944.pn. 6127210.pn. 6168980.pn. 6380016.pn.		
-	4	jp-10079517-\$.did. jp-02023651-\$.did.	USPAT;	2004/06/04 16:05
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	2004/05/00 44 00
-	4771	((thin adj film adj transistor) tft) same (cmos nmos pmos	USPAT;	2004/06/08 11:00
	225	complementary "p-type" "n-type")	US-PGPUB	2004/06/00 47:20
-	936	((thin adj film adj transistor) tft) same (cmos	USPAT;	2004/06/08 17:38
		complementary) same (channel with ("p-type" "p-doped"	US-PGPUB	
	F7F	type dop\$4))	LICDAT.	2004/06/09 17:17
-	575	((thin adj film adj transistor) tft) same ((cmos	USPAT;	2004/06/08 17:17
		complementary) with (channel near4 ("p-type" "p-doped"	US-PGPUB	
	169	type dop\$4))) (((this adi film adi transister) tft) same (smos	USPAT;	2004/06/08 11:11
•	109	(((thin adj film adj transistor) tft) same (cmos complementary) same (channel with ("p-type" "p-doped"	US-PGPUB	2004/00/00 11.11
		type dop\$4))) same ((impurit\$4 dop\$4 boron "p-type" "p	03-FGF00	
		type dops4))) same ((impunits4 dops4 boron p-type p type") near4 concentration)		
	0	6632711.URPN.	USPAT	2004/06/08 13:01
	0	6635521.URPN.	USPAT	2004/06/08 13:01
	139	((thin adj film adj transistor) tft) and (cmos complementary)	EPO; JPO;	2004/06/08 17:46
	133	and (channel with ("p-type" "p-doped" type dop\$4))	DERWENT;	200 1, 00, 00 27110
		and Chamie Mark p type p doped type dopt 1//	IBM_TDB	
_	2	jp-09186343-\$.did.	USPAT;	2004/06/08 17:15
	-)	US-PGPUB;	200 1, 00, 00 27 120
			EPO; JPO;	
			DERWENT	
_	3951	257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls.	USPAT;	2004/06/08 17:16
	3331	345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.	US-PGPUB	
_	393	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls.	USPAT;	2004/06/08 17:19
	333	345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and	US-PGPUB	, ,
		((thin adj film adj transistor) tft) and ((cmos		
		complementary) same (channel with ("p-type" "p-doped"		
		type dop\$4)))		
	106	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls.	USPAT;	2004/06/08 17:26
		345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and	US-PGPUB	, .
		((thin adj film adj transistor) tft) and ((cmos		
		complementary) same (channel near4 ("p-type" "p-doped"		
		dop\$4)))		
-	938	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls.	USPAT;	2004/06/08 17:44
		345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and	US-PGPUB	
		(channel with (impurit\$4 dop\$4) with ("p-type" "p type"		
		"p-doped" "p doped" boron))		
-	180	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls.	USPAT;	2004/06/08 17:42
		345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and	US-PGPUB	
		((cmos complementary) same (channel with (impurit\$4	1	
		dop\$4) with ("p-type" "p type" "p-doped" "p doped" boron)))	<u> </u>	

Search History 6/9/04 1:49:54 PM Page 1

-	447	(257/59.ccls. 257/66.ccls. 257/72.ccls. 257/351.ccls.	USPAT;	2004/06/08 17:43
		345/92.ccls. 438/153.ccls. 438/154.ccls. 438/217.ccls.) and	US-PGPUB	
		((thin adj film adj transistor) tft) and (cmos complementary)		
		and (channel with (impurit\$4 dop\$4) with ("p-type" "p type"		
		"p-doped" "p doped" boron))		
-	2243	(channel with (impurit\$4 dop\$4) with ("p-type" "p type"	EPO; JPO;	2004/06/08 17:47
		"p-doped" "p doped" boron))	DERWENT;	
			IBM_TDB	
-	533	((channel with (impurit\$4 dop\$4) with ("p-type" "p type"	EPO; JPO;	2004/06/08 17:48
		"p-doped" "p doped" boron))) and ((thin adj film adj	DERWENT;	•
		transistor) tft cmos complementary)	IBM_TDB	
-	884	((channel near4 (impurit\$4 dop\$4)) with ("p-type" "p type"	EPO; JPO;	2004/06/08 17:47
		"p-doped" "p doped" boron))	DERWENT;	
			IBM_TDB	
-	222	(((channel near4 (impurit\$4 dop\$4)) with ("p-type" "p type"	EPO; JPO;	2004/06/08 17:48
		"p-doped" "p doped" boron))) and ((thin adj film adj	DERWENT;	
		transistor) tft cmos complementary)	IBM_TDB	